MMBT589LT1G, NSVMMBT589LT1G

High Current Surface Mount PNP Silicon Switching Transistor for Load Management in Portable Applications

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-30	Vdc
Collector - Base Voltage	V _{CBO}	-50	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-1.0	Adc
Collector Current – Peak	I _{CM}	-2.0	Α

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	310 2.5	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	403	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	710 5.7	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	176	°C/W
Total Device Dissipation (Ref. Figure 8) (Single Pulse < 10 sec.)	P _{Dsingle}	575	mW
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 X 1.0 inch Pad



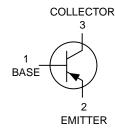
ON Semiconductor®

www.onsemi.com

30 VOLTS, 2.0 AMPS PNP TRANSISTORS



SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



G3 = Device Code M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT589LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBT589LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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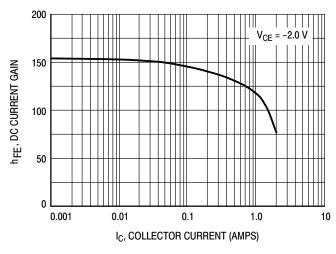
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage $(I_C = -10 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	 -30	_	Vdc
Collector – Base Breakdown Voltage (I _C = -0.1 mAdc, I _E = 0)	V _(BR) CBO	-50	-	Vdc
Emitter – Base Breakdown Voltage (I _E = -0.1 mAdc, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	Ісво	-	-0.1	μAdc
Collector–Emitter Cutoff Current (V _{CES} = -30 Vdc)	I _{CES}	_	-0.1	μAdc
Emitter Cutoff Current (V _{EB} = -4.0 Vdc)	I _{EBO}	_	-0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) (Figure 1) $ \begin{aligned} &(I_C = -1.0 \text{ mA, } V_{CE} = -2.0 \text{ V}) \\ &(I_C = -500 \text{ mA, } V_{CE} = -2.0 \text{ V}) \\ &(I_C = -1.0 \text{ A, } V_{CE} = -2.0 \text{ V}) \\ &(I_C = 2.0 \text{ A, } V_{CE} = -2.0 \text{ V}) \end{aligned} $	h _{FE}	100 100 80 40	300 - -	-
Collector – Emitter Saturation Voltage (Note 3) (Figure 3) $ \begin{pmatrix} I_C = -0.5 \text{ A}, I_B = -0.05 \text{ A} \end{pmatrix} $ $ \begin{pmatrix} I_C = -1.0 \text{ A}, I_B = 0.1 \text{ A} \end{pmatrix} $ $ \begin{pmatrix} I_C = -2.0 \text{ A}, I_B = -0.2 \text{ A} \end{pmatrix} $	V _{CE(sat)}	- - -	-0.25 -0.30 -0.65	V
Base – Emitter Saturation Voltage (Note 3) (Figure 2) $(I_C = -1.0 \text{ A}, I_B = -0.1 \text{ A})$	V _{BE(sat)}	_	-1.2	V
Base – Emitter Turn–on Voltage (Note 3) (I _C = -1.0 A, V _{CE} = -2.0 V)	V _{BE(on)}	-	-1.1	V
Cutoff Frequency ($I_C = -100 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$, $f = 100 \text{ MHz}$)	f⊤	100	_	MHz
Output Capacitance (f = 1.0 MHz)	Cobo	_	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%

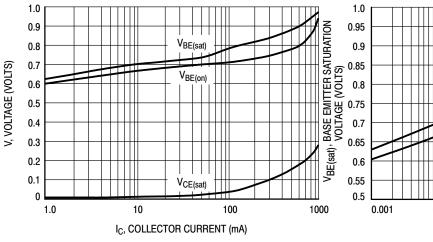
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230 $V_{CE} = -1.0 V$ 210 125°C 190 hFE, DC CURRENT GAIN 170 150 25°C 130 110 90 -55°C 70 50 1.0 10 100 1000 IC, COLLECTOR CURRENT (mA)

Figure 1. DC Current Gain versus Collector Current

Figure 2. DC Current Gain versus Collector Current



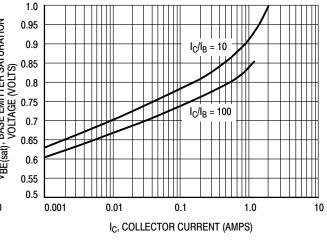
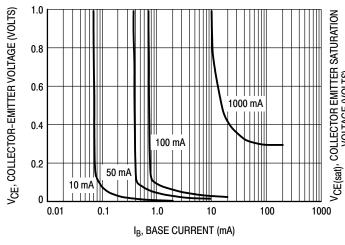


Figure 3. "On" Voltages

Figure 4. Base Emitter Saturation Voltage versus Collector Current



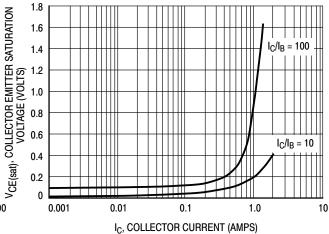


Figure 5. Collector Emitter Saturation Voltage versus Collector Current

Figure 6. Collector Emitter Saturation Voltage versus Collector Current

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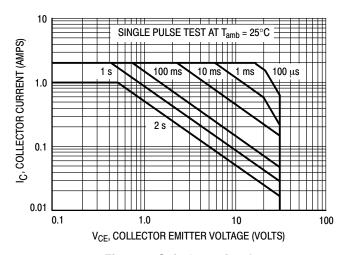


Figure 7. Safe Operating Area

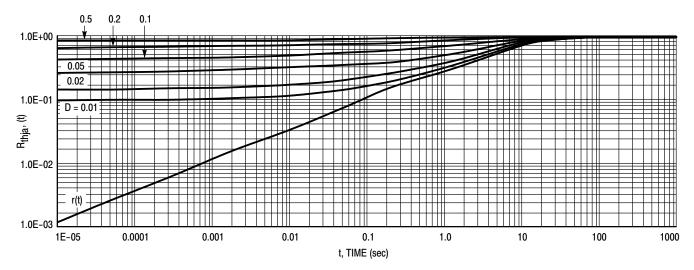


Figure 8. Normalized Thermal Response

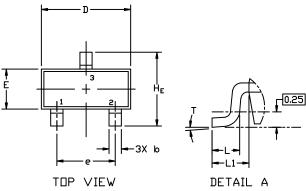




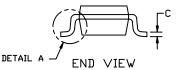
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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

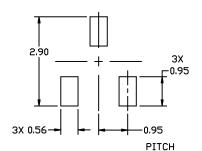


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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